



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Evgeni Gousev et. al.

Serial No.: 10/672,631

Group No.: 2812

Filed: 09/27/2003

Examiner: GURLEY, LYNNE ANN

For: **Thin germanium oxynitride gate dielectric for germanium-based devices**

**Commissioner for Patents
Alexandria, VA 22313-1450**

INFORMATION DISCLOSURE STATEMENT

The attached form 1449 (Modified) gives references pertaining to the above application.

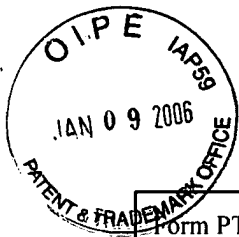
Respectfully,

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Sheet 1 of 1

Form PTO 1449 (modified)				Docket No <u>YOR920030463US1</u>		Serial No <u>10/672,631</u>	
LIST OF PRIOR ART CITED BY APPLICANT				Applicant <u>Evgeni Gousev et. al.</u>			
				Filing Date <u>09/27/2003</u>		Group 2812	
U. S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date
	AA	5,241,214	08/31/1993	Herbots	257	649	04/29/1991
	AB	5,571,734	11/05/1996	Tseng	438	591	10/03/1994
U. S. PUBLISHED APPLICATIONS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date
	AA	20020197886	12/26/2002	Niimi	438	783	06/20/2001
OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
	AA	BERA L K ET AL: "HIGH QUALITY GATE DIELECTRICS GROWN BY RAPID THERMAL PROCESSING USING SPLIT-N20 TECHNIQUE ON STRAINED SI(0.91)GE(0.09) FILMS" IEEE ELECTRON DEVICE LETTERS, vol. 22, no. 8, pages 387-389, August 2001					
	AB	MAIKAP S ET AL: "NO/O2/NO PLASMA-GROWN OXYNITRIDE FILMS ON STRAINED-SI(1-X)GE(X)" ELECTRONICS LETTERS, vol. 35, no. 14, pages 1202-1203, July 1999					
	AC	GREGORY O. J. AT AL.: "ELECTRICAL CHARACTERIZATION OF SOME NATIVE INSULATORS ON GERMANIUM" MATERIALS RESEARCH SOCIETY SYMPOSIUM, PROCEEDINGS vol. 76, pages 307-311, 1987					
Examiner				Date Considered			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant							